

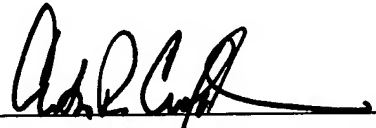
REMARKS

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page(s) is captioned "Version With Markings To Show Changes Made."

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: _____



Arthur R. Crawford
Reg. No. 25,327

ARC:ecb
1100 North Glebe Road, 8th Floor
Arlington, VA 22201-4714
Telephone: (703) 816-4000
Facsimile: (703) 816-4100

204033-9996T007

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION

Page 1, before the first line, insert as a separate paragraph:

This application is the US national phase of international application
PCT/GB00/02571 filed 05 July 2000, which designated the US.

IN THE CLAIMS

4. A method according to claim 1, ~~2 or 3~~ wherein the printed circuit conductor pattern includes conductor regions less than about 30 microns wide.

5. A method according to claim 1, ~~2, 3 or 4~~ wherein the printed circuit conductor pattern includes conductor regions spaced by less than about 30 microns.

6. A method according to ~~any one of the preceding claims~~ 1 wherein the etch band is less than about 30 microns wide.

7. A mask for use in producing a resist pattern for etching of a printed circuit, the mask being produced by the method of ~~any one of the preceding claims~~ 1.

10. A printed circuit according to claim 8 ~~or 9~~ wherein the etch band is of substantially the same width as the narrowest conductor or the narrowest separation between conductors in the printed circuit

11. A printed circuit according to claim 8, ~~9 or 10~~ wherein the printed circuit conductor pattern includes conductor regions less than about 30 microns wide.

12. A printed circuit according to claim 8, ~~9, 10 or 11~~ wherein the printed circuit conductor pattern includes conductor regions spaced by less than about 30 microns.

13. A printed circuit according to ~~any one of~~ claims 8 to 12 wherein the etch band is less than 30 microns wide.

16. A method according to claim 14 ~~or 15~~ wherein the pattern includes conductor elements spaced by less than about 30 microns.

17. A method according to claim 14, ~~15 or 16~~ wherein the regions of constant width are of substantially the same width as the narrowest element or narrowest separation between elements in the printed circuit.

~~18. A mask or a printed circuit substantially as hereinbefore described with reference to and as illustrated in figures 1 and 3 of the accompanying drawings.~~

~~19. A method of producing a mask or a printed circuit substantially as hereinbefore described.~~